

- Adoption of FBET process
- AF amp, AF power amp
- High breakdown voltage $V_{CEO} > 80V$

Collector to Base Voltage	V_{CB0}	(-)100	V
Collector to Emitter Voltage	V_{CE0}	(-)80	V
Emitter to Base Voltage	V_{EB0}	(-)5	V
Collector Current	I_C	(-)500	mA
Collector Current (Pulse)	I_{CP}	(-)800	mA
Base Current	I_B	(-)100	mA
Collector Dissipation	P_C	600	mW
Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	-55 to +150	°C

Collector Cutoff Current	I_{CBO}	$V_{CB}=(-)60V, I_E=0$	$(-)0.1$	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=(-)4V, I_C=0$	$(-)0.1$	μA
DC Current Gain	$h_{FE}(1)$	$V_{CE}=(-)5V, I_C=(-)50mA$	100※	400※
	$h_{FE}(2)$	$V_{CE}=(-)5V, I_C=(-)400mA$	60	
Gain-Bandwidth Product	f_T	$V_{CE}=(-)10V, I_C=(-)10mA$	120	MHz
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C=(-)400mA, I_B=(-)40mA$	0.16	V
			(-0.2)	(-0.5)
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C=(-)400mA, I_B=(-)40mA$	$(-)0.9$	$(-)1.2$
Output Capacitance	c_{ob}	$V_{CB}=(-)10V, f=1MHz$	(7)5	pF
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C=(-)10\mu A, I_E=0$	$(-)100$	V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C=(-)1mA, R_{BE}=\infty$	$(-)80$	V
E-B Breakdown Voltage	$V_{(BR)ERO}$	$I_E=(-)10\mu A, I_C=0$	$(-)5$	V

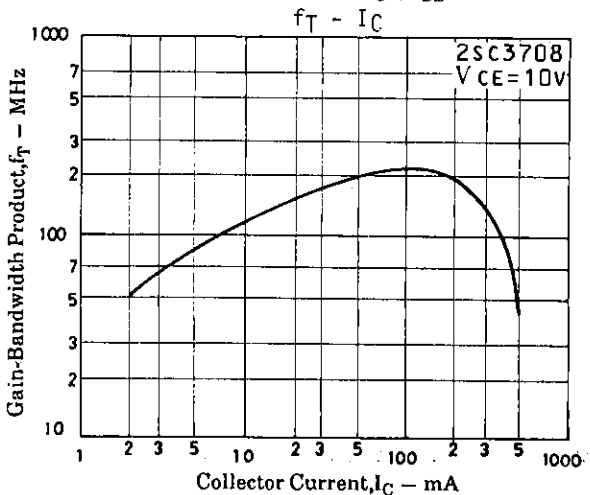
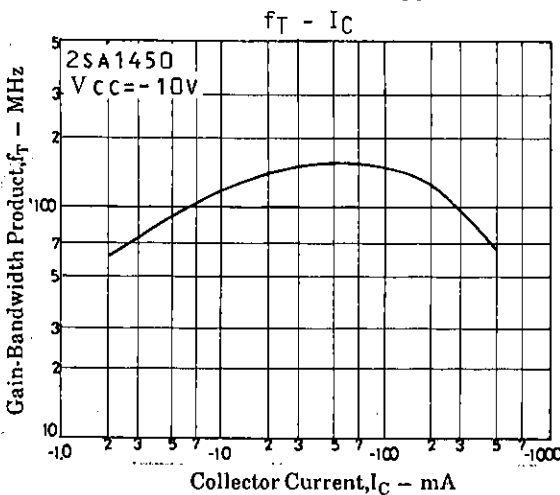
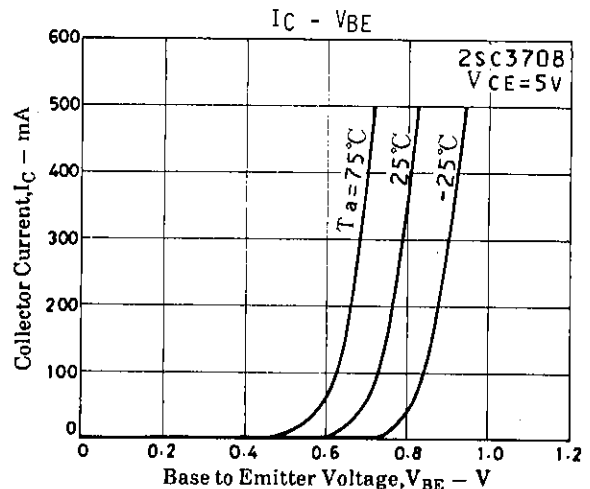
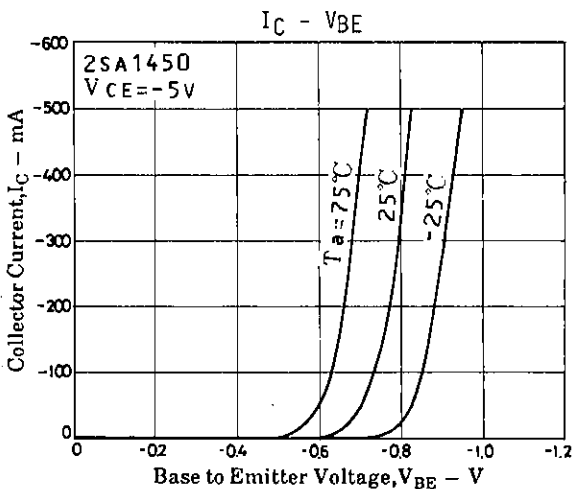
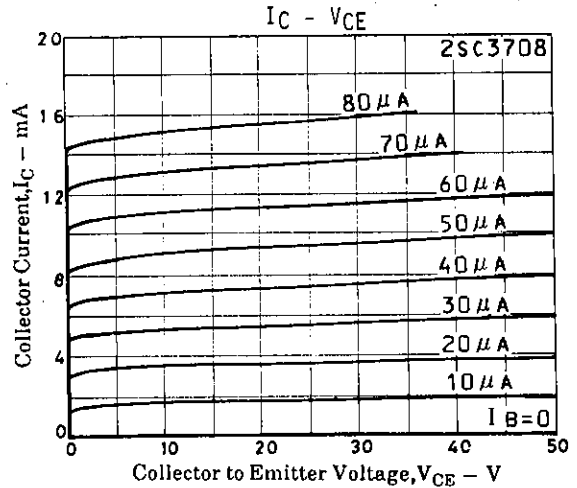
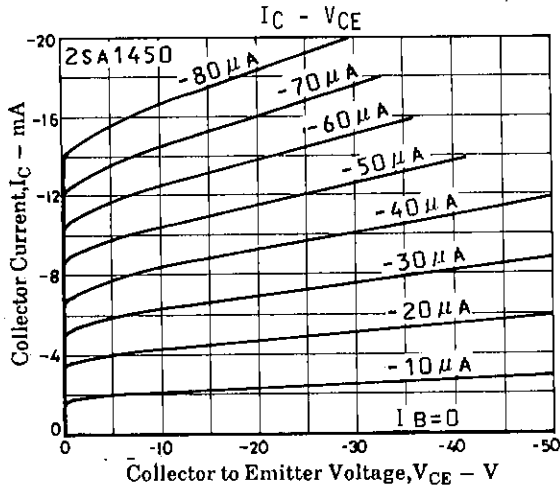
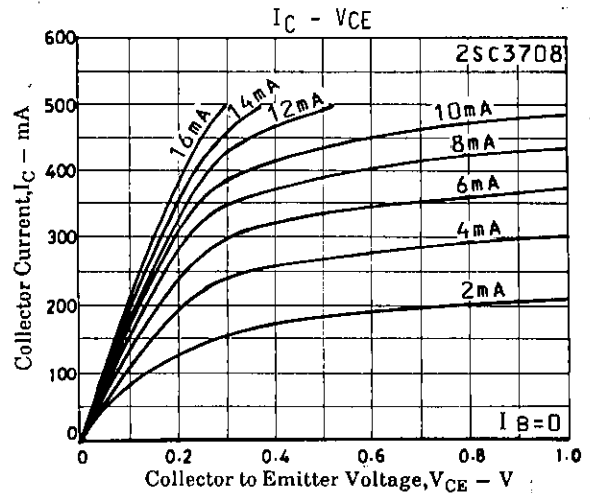
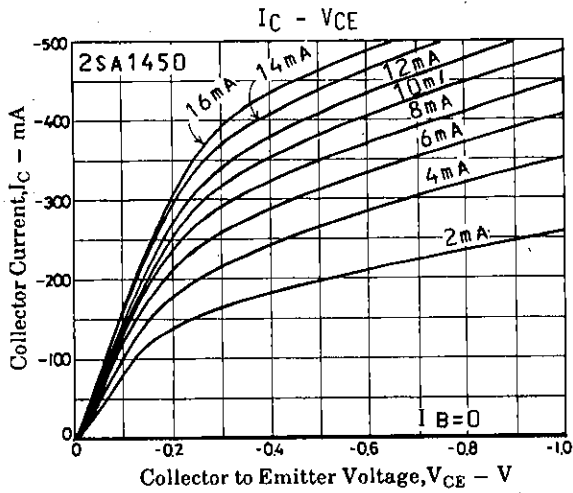
100	R	200	140	S	280	200	T	400
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JEDEC: TO-92
EIAJ: SC-43
SANYO: NP

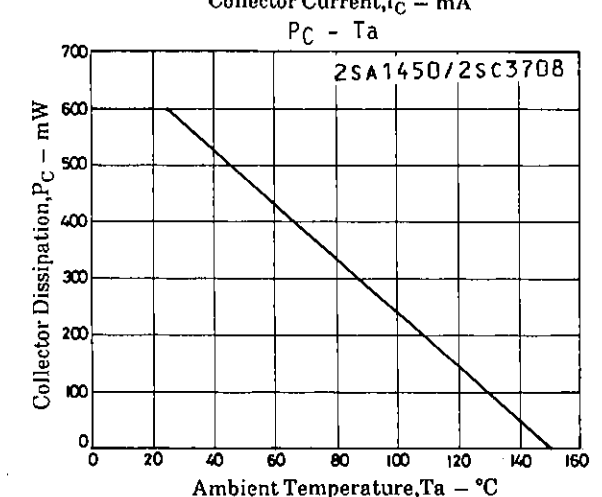
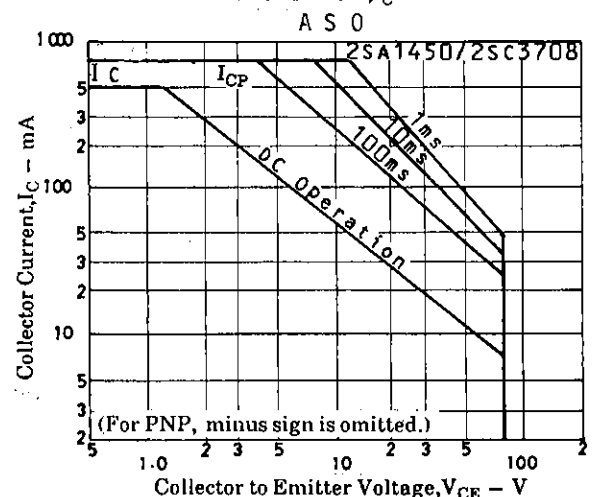
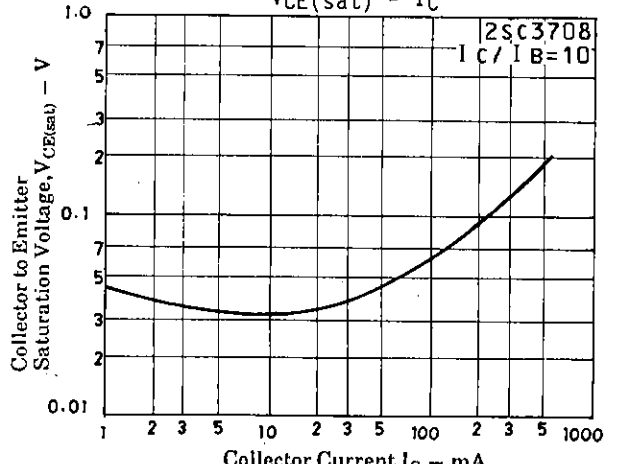
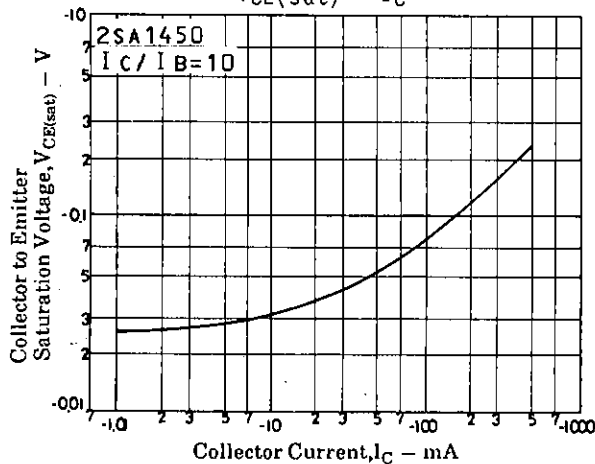
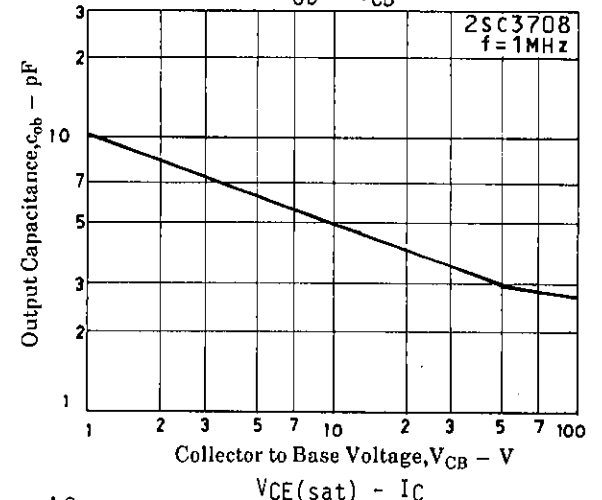
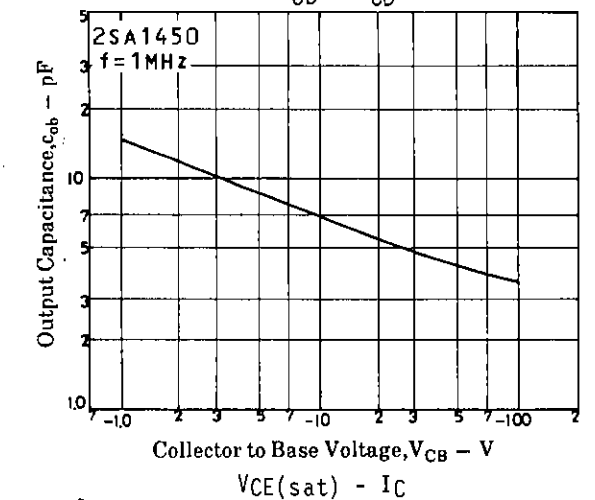
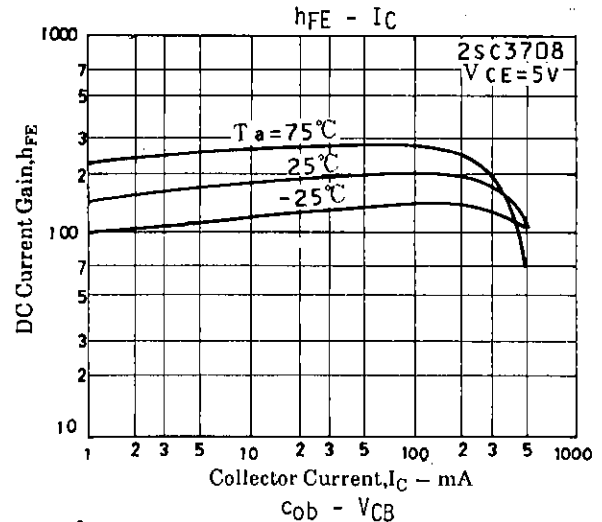
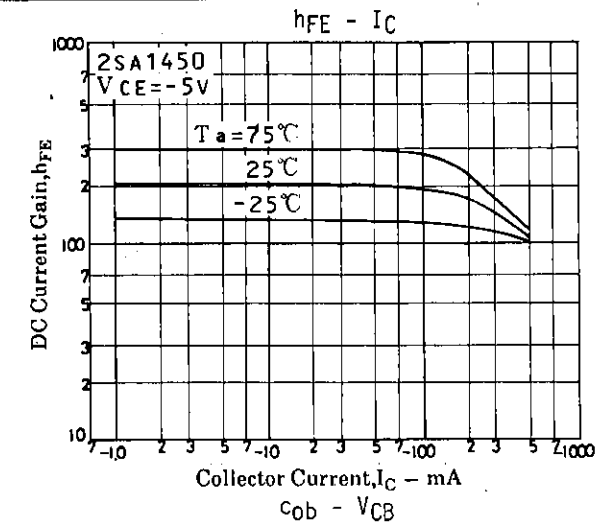
B: Base
C: Collector
E: Emitter

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